NSN 5961-01-276-9984

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-276-9984 **Inclosure Material:** Metal **Overall Length:** Between 1.030 inches and 1.095 inches Overall Diameter: Between 2.200 inches and 2.500 inches **Function For Which Designed:** Reverse blocking **Mounting Facility Quantity: Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1400.0 repetitive peak off-state voltage and 1400.0 repetitive peak reverse voltage and 1500.0 nonrepetitive peak reverse voltage and 5.0 peak negative gate voltage **Current Rating Per Characteristic:** 7000.00 amperes peak forward surge current nanoamperes and 4.00 amperes forward current, total rms of standard range **Power Rating Per Characteristic:** 3.0 watts small-signal input power, common-collector universal and 16.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Terminal Type And Quantity:** 1 quick disconnect, male and 1 turret and 2 insulated wire lead w/terminal lug **Specification Data:** 10001-2938688-5 manufacturers specification control Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: